

30 V, P-channel Trench MOSFET 17 April 2020

1. General description

P-channel enhancement mode MOSFET in an LFPAK56 (Power SO8) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

This product has been designed and qualified to AEC-Q101 standard for use in high-performance automotive applications such as reverse battery protection.

2. Features and benefits

- · High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Reverse battery protection
- Power management
- High-side load switch
- Motor drive

4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage		[1]	-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{mb} = 25 °C		-	-	-80	А
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	-	110	W
Static chara	octeristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = -10 V; I _D = -13.5 A; T _j = 25 °C		-	8	10	mΩ

[1] V_{GS} = -20 V/+5 V according AEC-Q101 at T_j = 175 °C; V_{GS} = -20 V/+20 V according AEC-Q101 at T_j = 150 °C

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	a	G (F Y
4	G	gate		s s
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	017aaa094

6. Ordering information

Table 3. Ordering information Type number Package								
Type number	Name	Description	Version					
BUK6Y10-30P	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669					

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK6Y10-30P	6Y1030P

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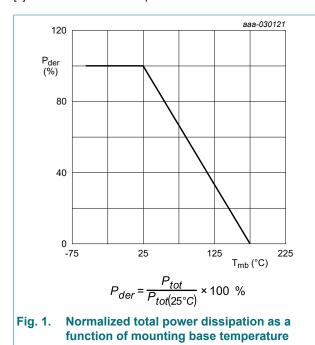
8. Limiting values

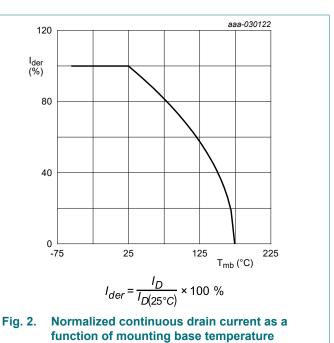
Table 5. Limiting values

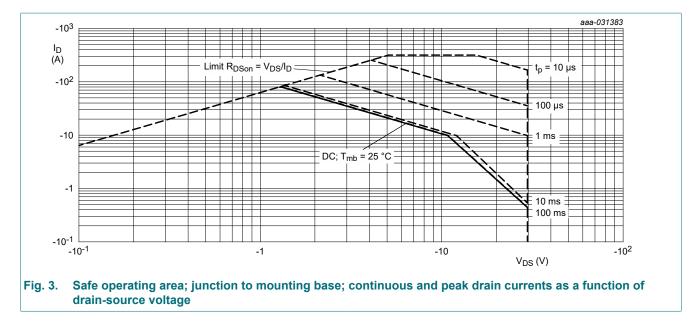
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage		[1]	-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{mb} = 25 °C		-	-80	А
		V _{GS} = -10 V; T _{mb} = 100 °C		-	-57	A
I _{DM}	peak drain current	single pulse; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	-320	А
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	110	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-dra	in diode					
Is	source current	T _{mb} = 25 °C		-	-80	А
I _{SM}	peak source current	single pulse; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$		-	-320	А
ESD maxim	num rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	800	V
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = -5.3 A; DUT in v avalanche (unclamped)		-	80	mJ

[1] $V_{GS} = -20 \text{ V/+5 V}$ according AEC-Q101 at T_j = 175 °C; $V_{GS} = -20 \text{ V/+20 V}$ according AEC-Q101 at T_j = 150 °C [2] Measured between all pins.





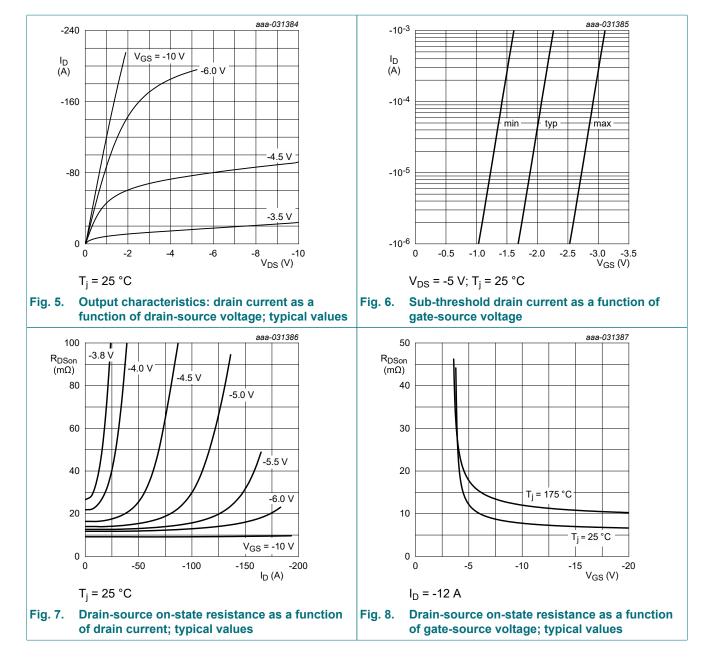


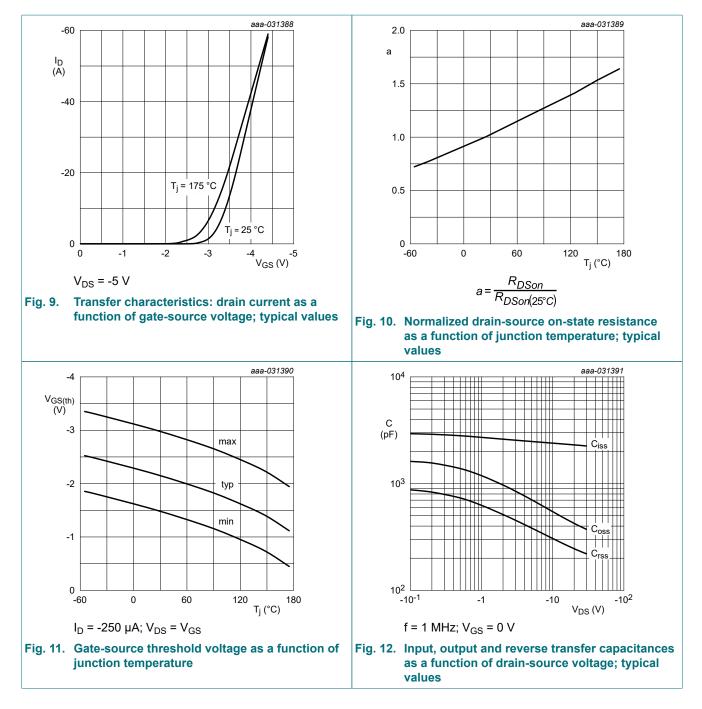
9. Thermal characteristics

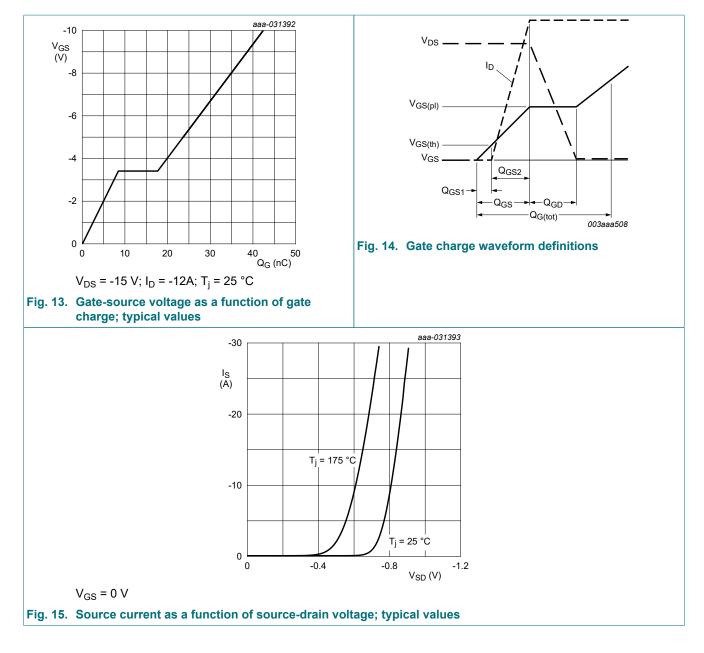
mbol	Parameter	Conditions	Min	Тур	Max	Unit
h(j-mb)	thermal resistance from junction to mounting base	n	-	1.1	1.4	K/W
10				а	aa-031187	
Z _{th(j-mb)}						
	ity cycle = 1					
1 = 0.7	0.50					
- 0.3	30					
	0.10					
10-1 0.0	05					
-0.	01 0.02					
10-2						
10 ⁻⁵	10-4	10 ⁻³ 10 ⁻²	10 ⁻¹	t (-)	1	
				t _p (s)		

10. Characteristics

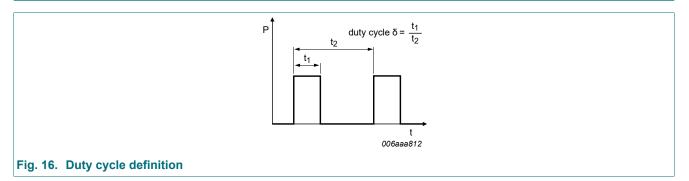
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = -250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	-1.5	-2	-3	V
I _{DSS}	drain leakage current	V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -30 V; V _{GS} = 0 V; T _j = 125 °C	-	-	-10	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = -10 V; I _D = -13.5 A; T _j = 25 °C	-	8	10	mΩ
	resistance	V _{GS} = -10 V; I _D = -13.5 A; T _j = 175 °C	-	13	16	mΩ
		V _{GS} = -4.5 V; I _D = -8.5 A; T _j = 25 °C	-	19	25	mΩ
9 _{fs}	forward transconductance	V _{DS} = -5 V; I _D = -13.5 A; T _j = 25 °C	-	31	-	S
R _G	gate resistance	f = 1 MHz	-	8.8	-	Ω
Dynamic ch	aracteristics		I			
Q _{G(tot)}	total gate charge	V _{DS} = -15 V; I _D = -12 A; V _{GS} = -10 V;	-	42.5	64	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	8.4	-	nC
Q _{GD}	gate-drain charge		-	9.3	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	2360	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	470	-	pF
C _{rss}	reverse transfer capacitance		-	270	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -15 V; I _D = -13.5 A; V _{GS} = -10 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	38	-	ns
t _{d(off)}	turn-off delay time		-	80	-	ns
t _f	fall time		-	580	-	ns
Source-drai	n diode					
V _{SD}	source-drain voltage	I _S = -80 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.7	-1.2	V
t _{rr}	reverse recovery time	I _S = -80 A; dI _S /dt = 100 A/μs;	-	24	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = -15 V; T _j = 25 °C	-	17	-	nC







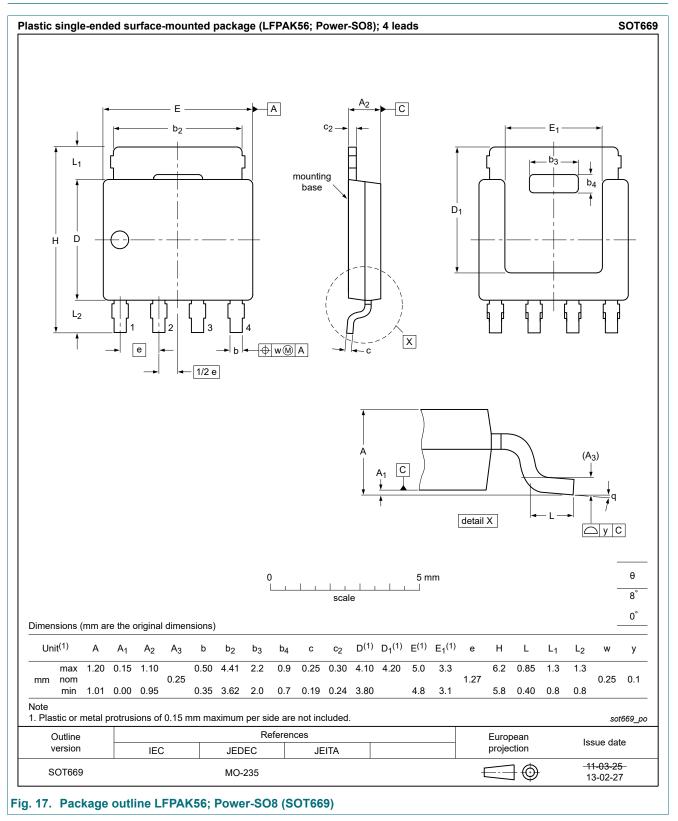
11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



13. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK6Y10-30P v.1	20200417	Product data sheet	-	-			

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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